

ABSTRACT OF THE DISCLOSURE

DEVICE FOR PRODUCTION OF COMPOUND SEMICONDUCTOR

A device for production of a compound semiconductor by means of a metal organic vapor phase epitaxy method, which has a structure that a metallic member is used at a part brought into contact with a gas at an upstream side of a flow of a raw material gas than a part for growing a compound semiconductor, and the metallic member is cooled to not higher than 300°C.

The present invention provides a device for production of a compound semiconductor with high productivity, which is suitable for the production of the compound semiconductor, using a metallic material wherein the processing precision is high and the risk of breakage is low.

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